The CNY17-X series combine an AlGaAs infrared emitting diode as the emitter which is oasc(c)4 (upli)6 dec

Storage Temperature	T_{stg}	-55+ 150	
Soldering Temperature	T_{sol}	260	

[illegible]

[illegible]

(Temperature=25℃)

Parameter		**Symbol**	**Condition**	**Min.**	**Typ.**	**Max.**	**Unit**
Input	Forward Voltage	V_F	I_F=10mA	-	1.27	1.4	V
			I_F=20mA	-	1.33	1.5	
	Reverse Current	I_R	V_R=6V	-	-	1	μA
	Input Capacitance	C_{in}	V=0, f=1MHz	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	V_{CE}=20V, I_F=0	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	I_C=0.1mA I_F=0	80	-	-	V
	Collector-Base breakdown voltage	BV_{CBO}	I_C=0.1mA I_F=0	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	I_E=0.1mA I_F=0	7	-	-	V
	Emitter-Base breakdown voltage	BV_{EBO}	I_E=0.1mA I_F=0	7	-	-	V
Transfer Characteristics	DC Forward current gain	h_{FE}	V_{CE}=5V, I_C=0.5mA	100	-	600	-
	Current transfer ratio	CTR	I_F=10mA V_{CE}=5V	40	-	320	%

FIG.1: Forward Current vs. Ambient Temperature

FIG.2: Collector Power Dissiption vs. Ambient Temperature

FIG.13: Test Circuits of Response Time

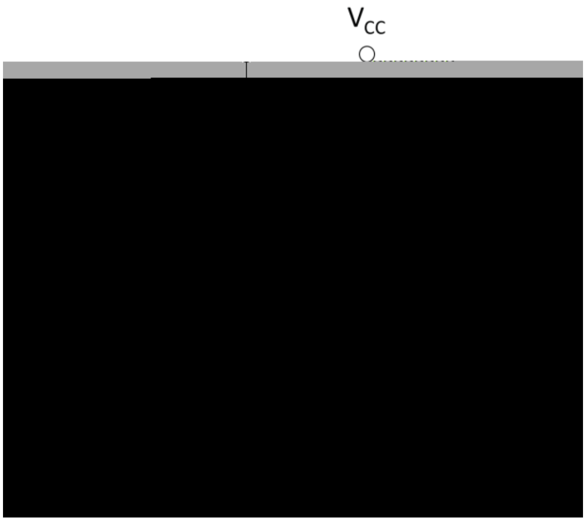
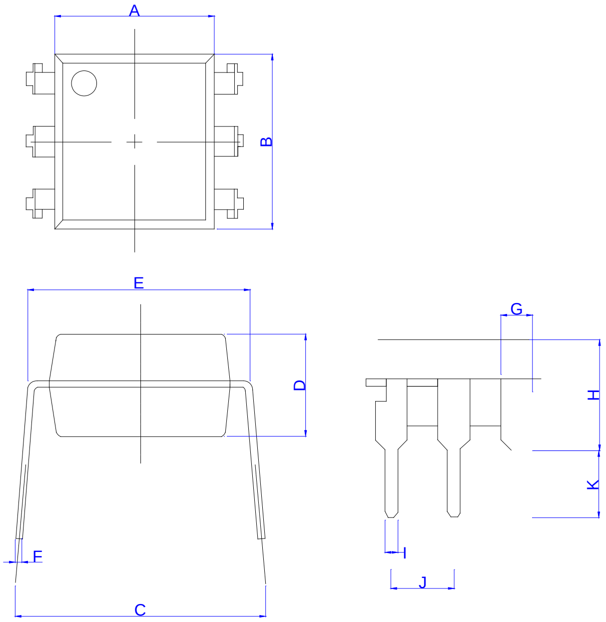


FIG.14: Curves of Response Time

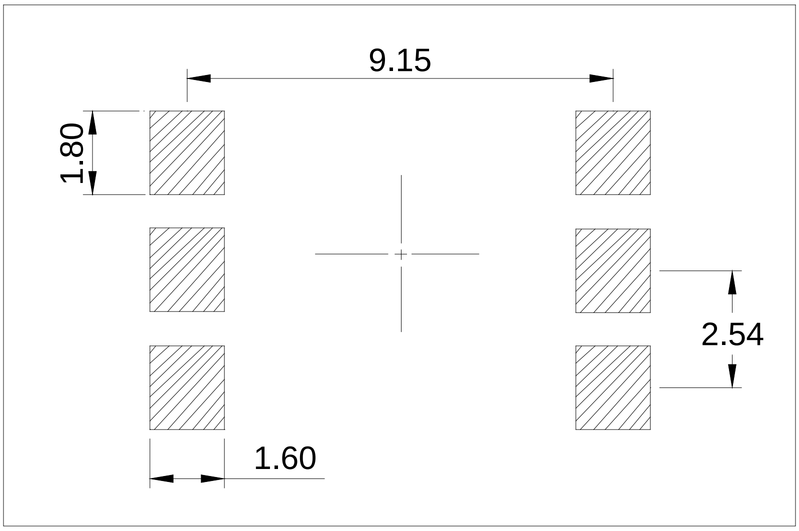
FIG.15: Test Circuits of FrequencyResponse

Standard DIP Type:

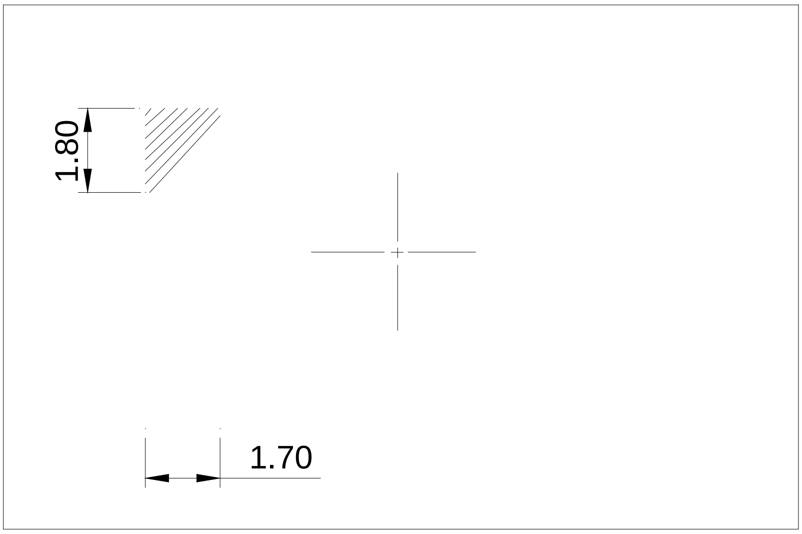


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.00		7.00	0.237		0.277
B	6.62		7.62	0.262		0.301
C	7.10		10.16	0.281		0.402
D	3.00		4.00	0.119		0.158
E	7.32		7.92	0.289		0.313
F						
G	0.90		1.50	0.036		0.059
H	3.50		4.80	0.138		0.190
I						
J						
K						

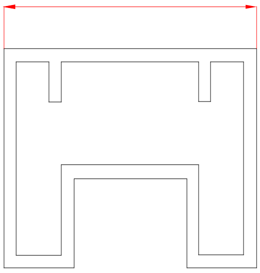
Option S

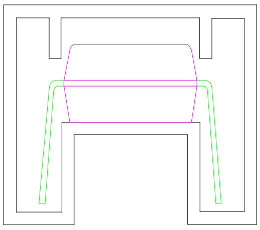


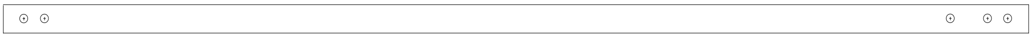
Option SL

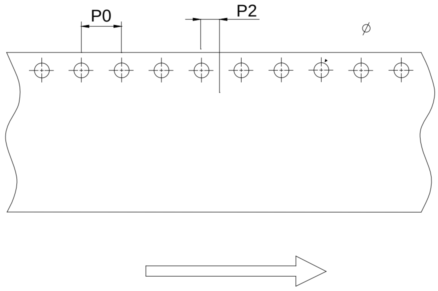


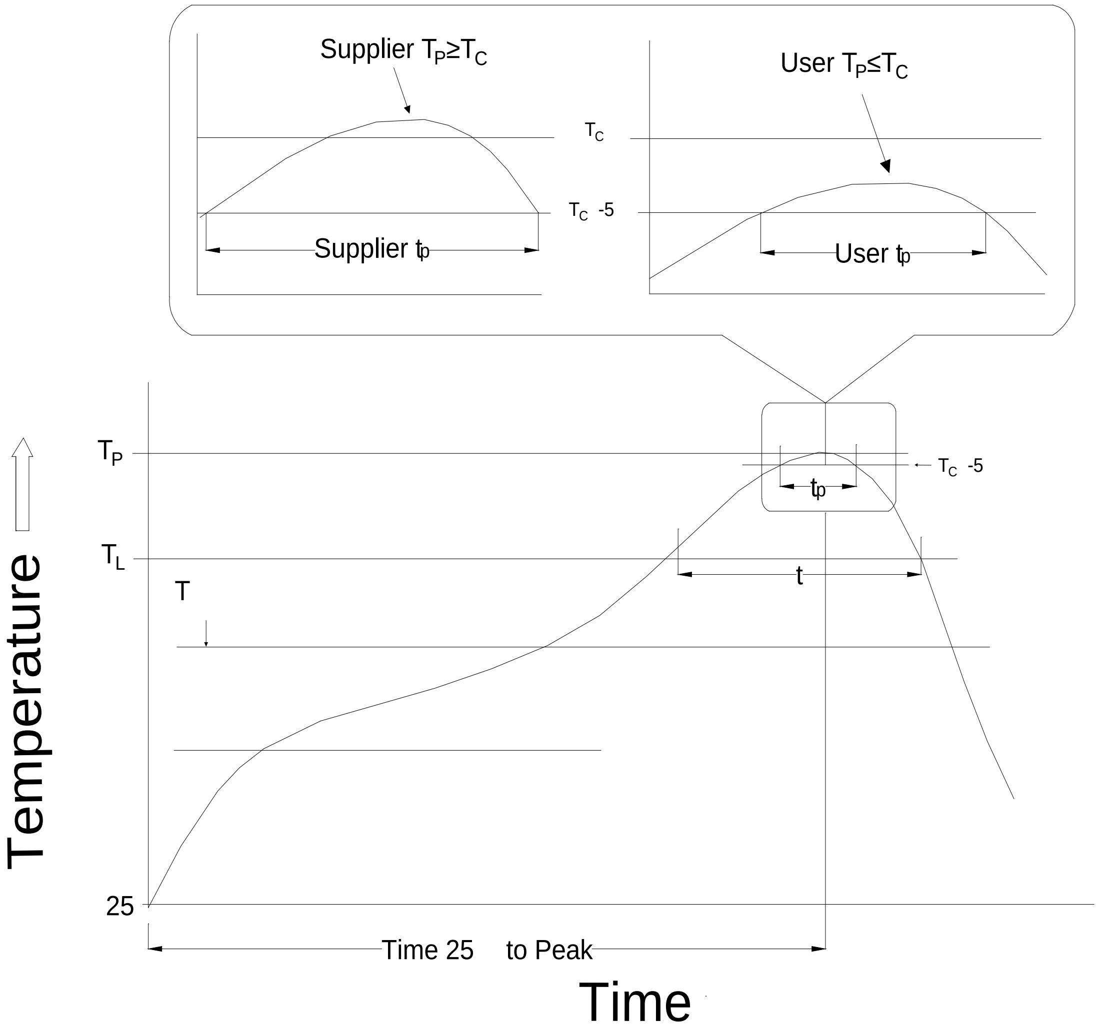
Standard DIP








P0
P2
⌀


Supplier $T_P \geq T_C$
T_C
T_C -5
Supplier t_P
User $T_P \leq T_C$
User t_P
T_P
T_C -5
t_P
T_L
T
t
25
Time 25 to Peak
Temperature
Time